## [METHOD FOR FORMING NITRIDED TUN-NEL OXIDE LAYE]

## **Abstract**

A method for forming a nitrided tunnel oxide layer is described. A silicon oxide layer as a tunnel oxide layer is formed on a semiconductor substrate, and a plasma nitridation process is performed to implant nitrogen atoms into the silicon oxide layer. A thermal drive-in process is then performed to diffuse the implanted nitrogen atoms across the silicon oxide layer.